

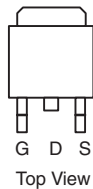
N-Channel 40-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
40	0.0023 at $V_{GS} = 10$ V	110 ^a
	0.0038 at $V_{GS} = 4.5$ V	

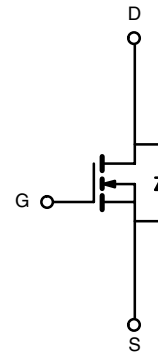
FEATURES

- TrenchFET[®] Power MOSFET
- New Package with Low Thermal Resistance


 Available
RoHS*
 COMPLIANT

TO-263


Ordering Information: SUM110N04-02L
 SUM110N04-02L-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	40	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	110 ^a	A
		$T_C = 125$ °C	110 ^a	
Pulsed Drain Current	I_{DM}	440		
Avalanche Current	I_{AR}	75		
Repetitive Avalanche Energy ^b	E_{AR}	L = 0.1 mH	280	mJ
Maximum Power Dissipation ^b		$T_C = 25$ °C	437.5 ^c	W
	$T_A = 25$ °C	3.75		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case (Drain)			

Notes:

- Package limited.
- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).

* Pb containing terminations are not RoHS compliant, exemptions may apply.

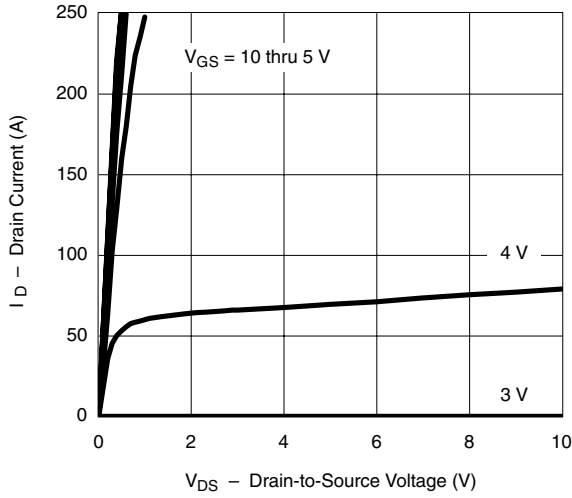
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	40			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1		3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	120			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 30\text{ A}$		0.00185	0.0023	Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 20\text{ A}$		0.0031	0.0038	
		$V_{GS} = 10\text{ V}$, $I_D = 30\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$			0.0037	
		$V_{GS} = 10\text{ V}$, $I_D = 30\text{ A}$, $T_J = 175\text{ }^\circ\text{C}$			0.0046	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 30\text{ A}$	30			S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		7300		μF
Output Capacitance	C_{oss}			1380		
Reverse Transfer Capacitance	C_{rss}			930		
Total Gate Charge ^c	Q_g	$V_{DS} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 110\text{ A}$		165	250	nC
Gate-Source Charge ^c	Q_{gs}			25		
Gate-Drain Charge ^c	Q_{gd}			55		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 30\text{ V}$, $R_L = 0.27\text{ }\Omega$ $I_D \cong 110\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_G = 2.5\text{ }\Omega$		30	45	ns
Rise Time ^c	t_r			80	120	
Turn-Off Delay Time ^c	$t_{d(off)}$			155	230	
Fall Time ^c	t_f			120	180	
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}$ ^b						
Continuous Current	I_S				110	A
Pulsed Current	I_{SM}				240	
Forward Voltage ^a	V_{SD}	$I_F = 85\text{ A}$, $V_{GS} = 0\text{ V}$		1.1	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 85\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		60	90	ns
Peak Reverse Recovery Charge	$I_{RM(REC)}$			2.6	4	A
Reverse Recovery Charge	Q_{rr}			0.08	0.15	μC

Notes:

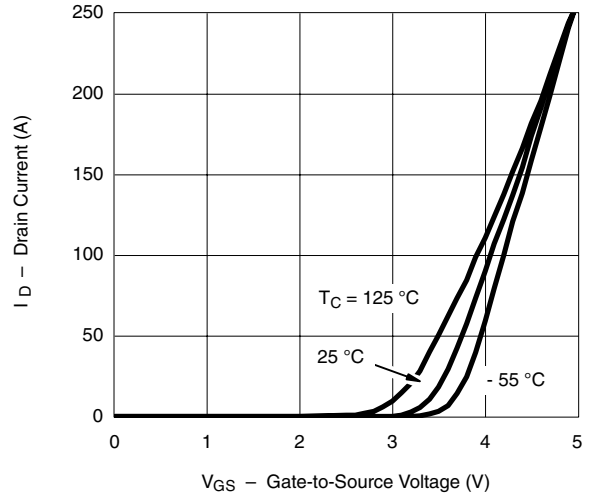
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

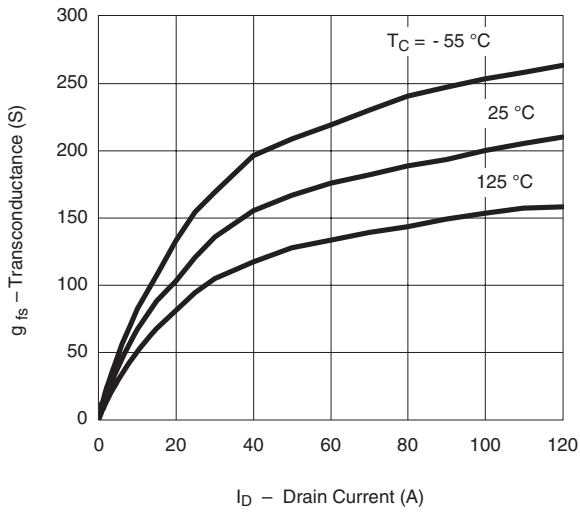
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



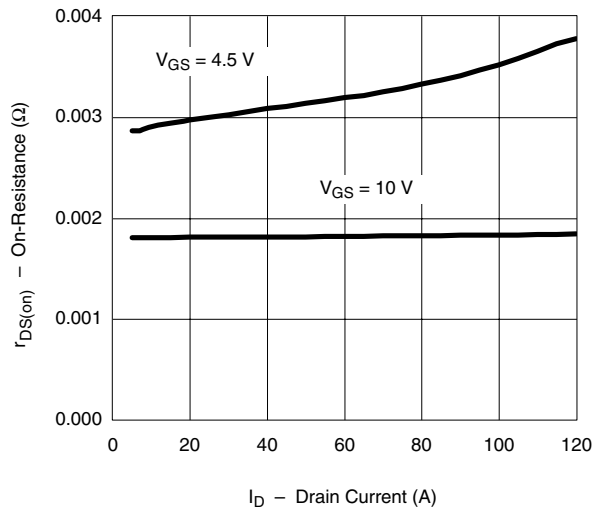
Output Characteristics



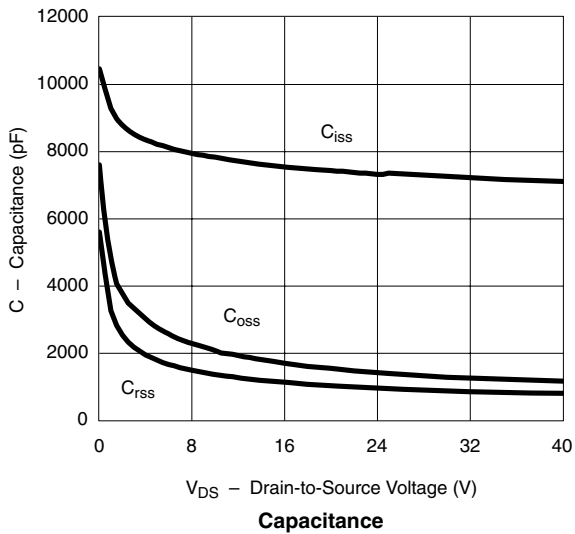
Transfer Characteristics



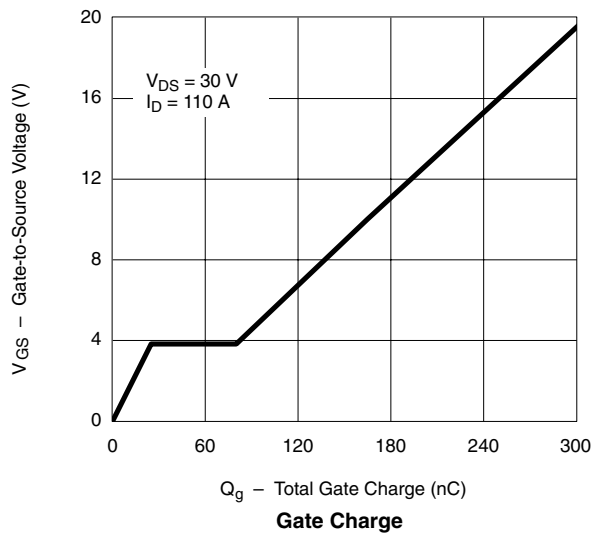
Transconductance



On-Resistance vs. Drain Current

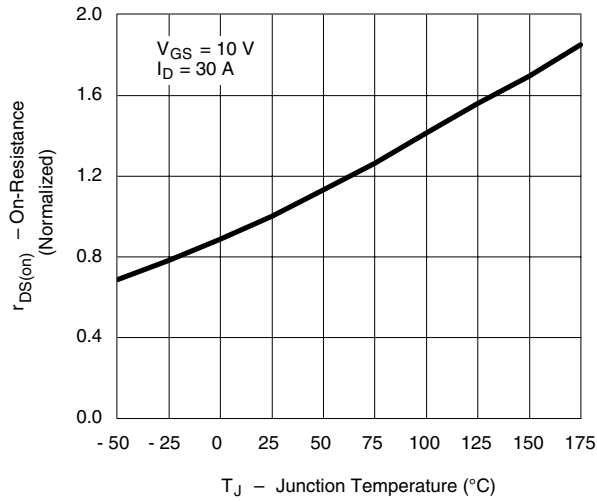


Capacitance

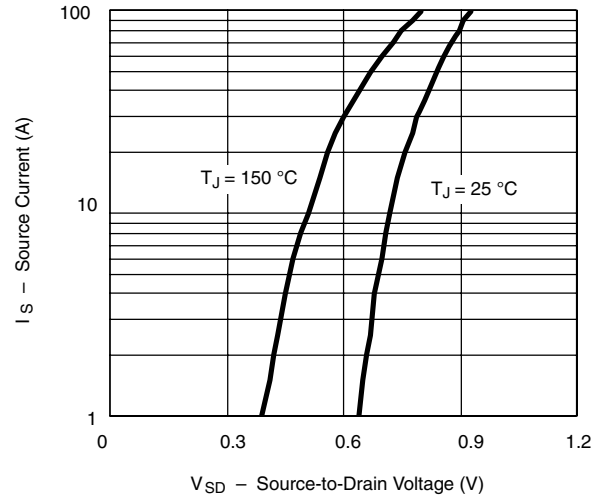


Gate Charge

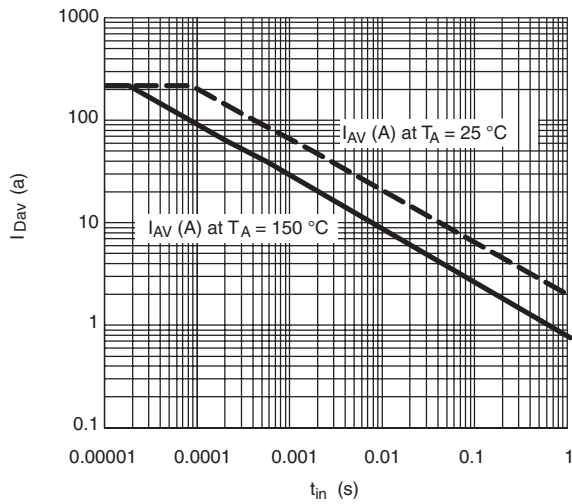
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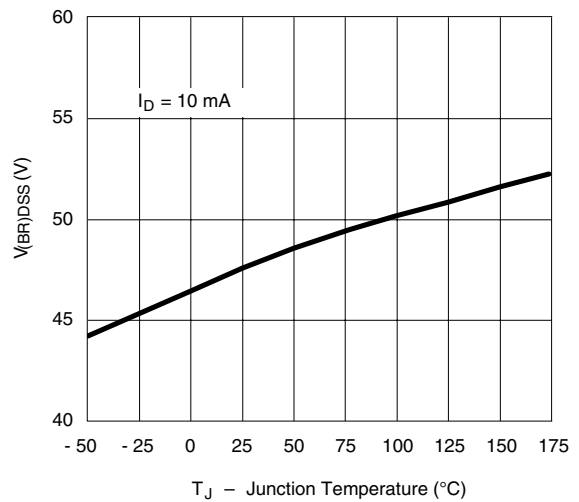
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

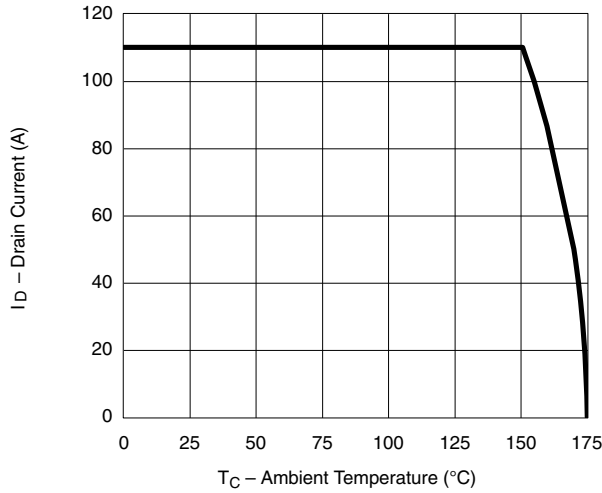


Avalanche Current vs. Time

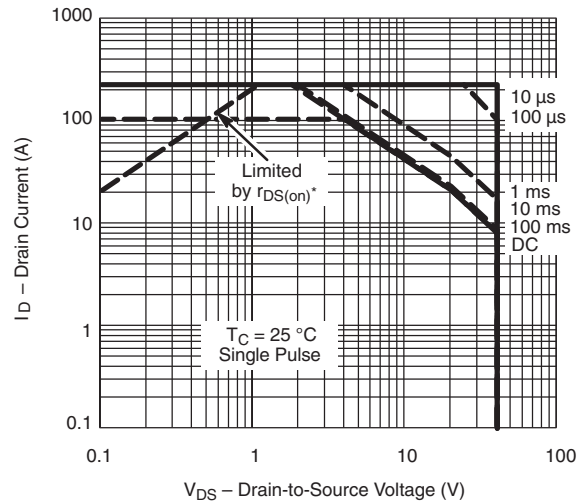


Drain Source Breakdown vs. Junction Temperature

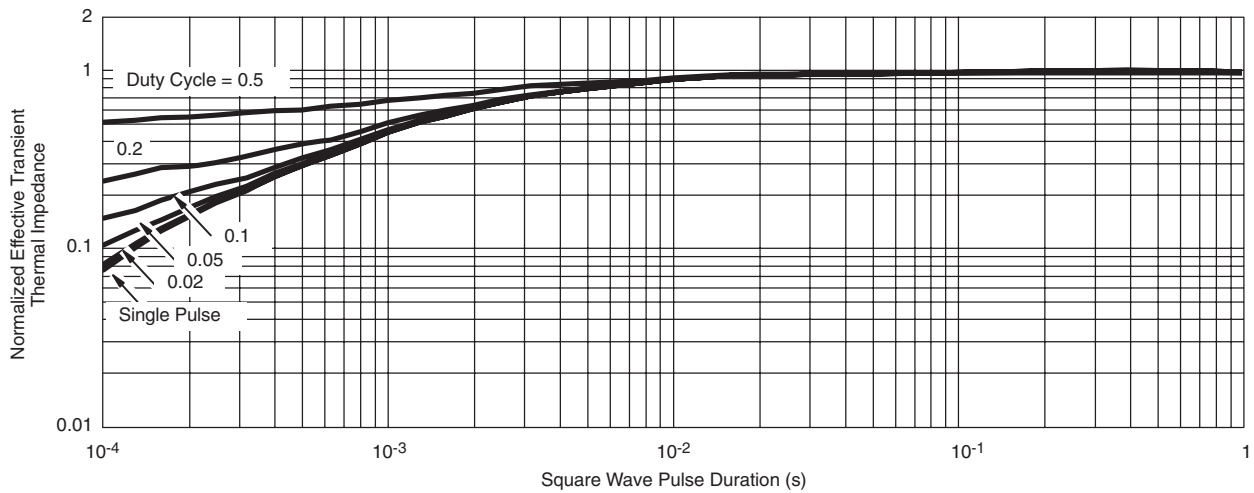
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area
* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Case

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